

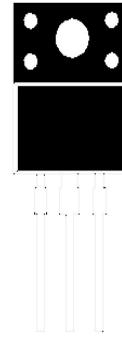
Product Character

- ◆ Half Bridge Rectified, Common Cathode Structure.
- ◆ Multilayer Metal -Silicon Potential Structure.
- ◆ Low Power Waste, High Efficiency.
- ◆ Beautiful High Temperature Character.
- ◆ Have Over Voltage protect loop, high reliability.
- ◆ RoHs Product.

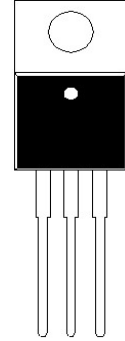
Primary Use

- ◆ Low Voltage High Frequency Switching Power Supply.
- ◆ Low Voltage High Frequency Invers Circuit.
- ◆ Low Voltage Continued Circuit and Protection Circuit.

Package



ITO-220AB



TO-220AB

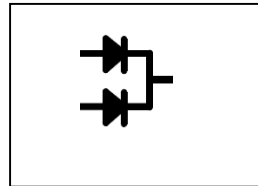
Summarize

MBR30150 Schottky diode, in the manufacture uses the main process technology includes: Silicon epitaxial substrate, P+ loop technology, The potential metal and the silicon alloy technology, the device uses the two chip, the common cathode, the plastic half package structure.

Typical Reference Data

VRRM=150V IF(AV)= 30A

Internal Equivalent Principle



Absolute Maximum Ratings

Item	Symbol	Data	Unit
Maximal Inverted Repetitive Peak Voltage	VRRM	150	V
maximal DC interdiction voltage	VDC	150	V
Average rectified forward current IC=150°C Whole Device unilateral	IFAV	30	A
		15	
Forward Peak Surge Current (Rated Load 8.3 Half Mssine Wave-According to JEDEC Method)	IFSM	150	A
Operating Junction Temperature	TJ	-40- +170	°C
Storage Temperature	TSTG	-40- +170	°C

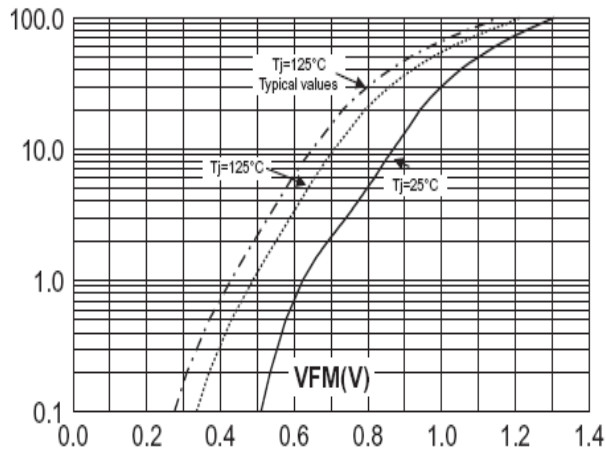
Electricity Character

Item	Test Condition		Minimum	representative	Maximum Value	Unit
IR	TJ =25°C	VR=VRRM			100	uA
	TJ =125°C				10	mA
VF	TJ =25°C	IF=15A			0.95	v

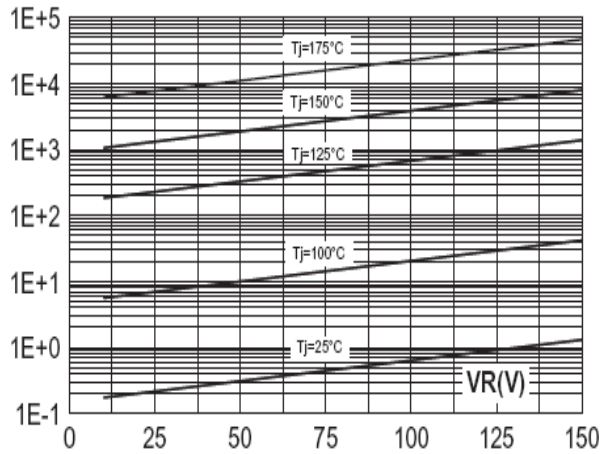


Character Curve

The forward voltage and forward current curve.



The reverse leak current and the reverse voltage (single-device) curve.



The crunode capacitance curve

